

# 2SC5846G

## Silicon NPN epitaxial planar type

For general amplification

### ■ Features

- High forward current transfer ratio  $h_{FE}$
- SSS-mini type package, allowing downsizing and thinning of the equipment and automatic insertion through the tape packing

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	60	V
Collector-emitter voltage (Base open)	$V_{CEO}$	50	V
Emitter-base voltage (Collector open)	$V_{EBO}$	7	V
Collector current	$I_C$	100	mA
Peak collector current	$I_{CP}$	200	mA
Collector power dissipation	$P_C$	100	mW
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

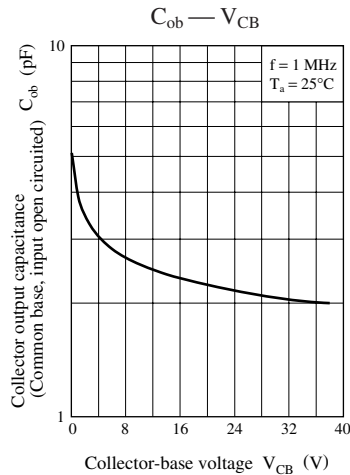
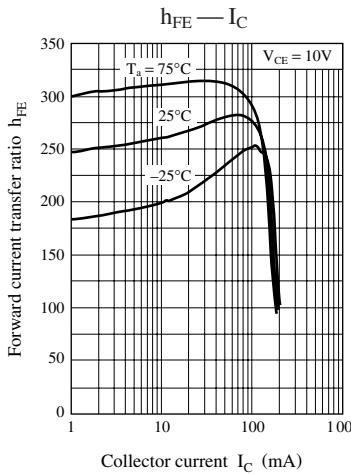
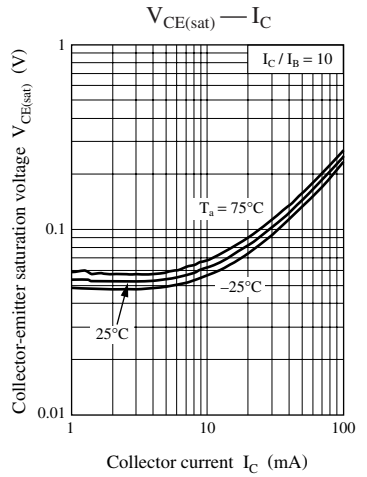
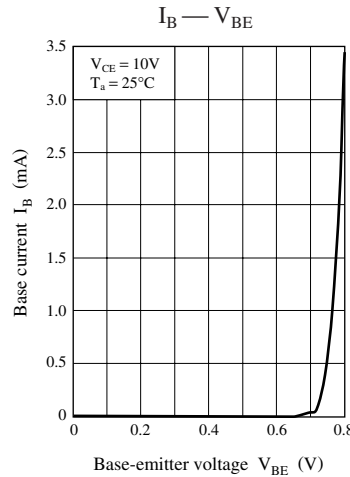
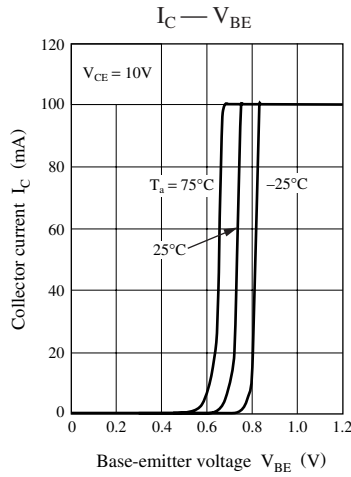
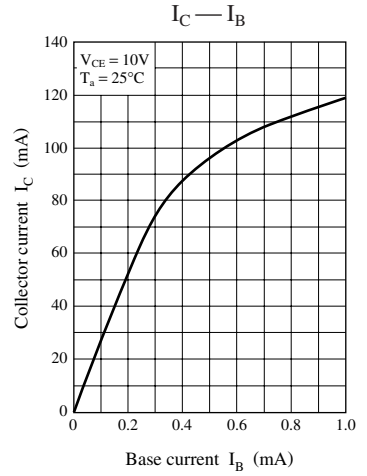
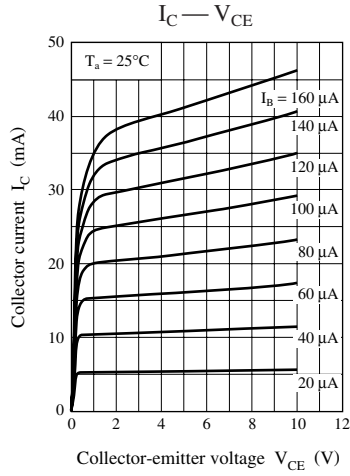
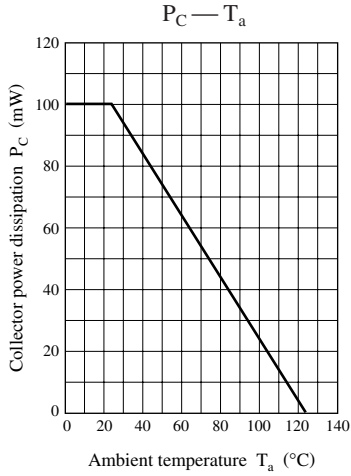
### ■ Package

- Code  
SSSMini3-F2
- Marking Symbol: 7K
- Pin Name
  1. Base
  2. Emitter
  3. Collector

### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

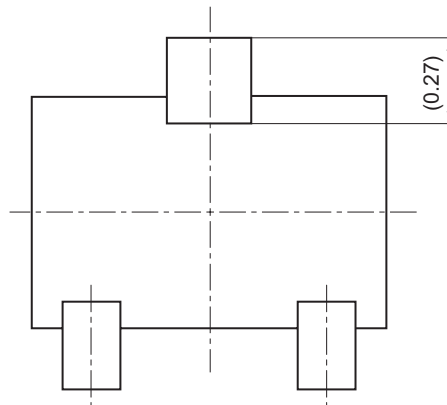
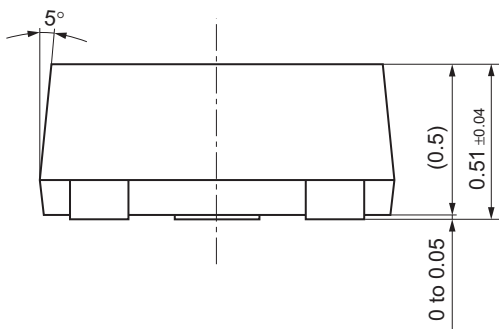
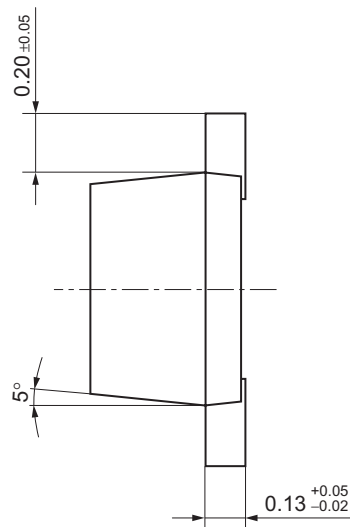
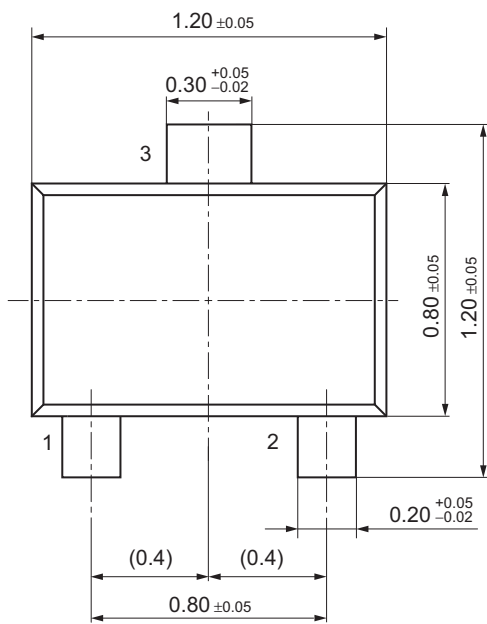
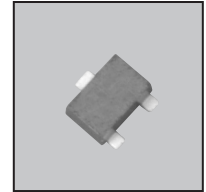
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 10 \mu\text{A}$ , $I_E = 0$	60			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 2 \text{ mA}$ , $I_B = 0$	50			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = 10 \mu\text{A}$ , $I_C = 0$	7			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 20 \text{ V}$ , $I_E = 0$			0.1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = 10 \text{ V}$ , $I_B = 0$			100	$\mu\text{A}$
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 10 \text{ V}$ , $I_C = 2 \text{ mA}$	180		390	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 100 \text{ mA}$ , $I_B = 10 \text{ mA}$		0.1	0.3	V
Collector output capacitance (Common base, input open circuited)	$C_{ob}$	$V_{CB} = 10 \text{ V}$ , $I_E = 0$ , $f = 1 \text{ MHz}$		2.2		pF
Transition frequency	$f_T$	$V_{CB} = 10 \text{ V}$ , $I_E = -2 \text{ mA}$ , $f = 200 \text{ MHz}$		100		MHz

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



SSSMini3-F2

Unit: mm



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